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APPLICATION NO), [FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/625,544		07/24/2003	Naokatsu Ikegami	02DCOAI010-CA	8199
26071	7590 12/17/2004		EXAMINER		
JUNICHI	MIMUR.	A	POTTER, ROY KARL		
OKI AME	RICA INC	•			
1101 14TH	I STREET,	N.W.	ART UNIT	PAPER NUMBER	
SUITE 555			2822		
WASHING	GTON, DO	20005	DATE MAILED: 12/17/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)				
		10/625,544	IKEGAMI, NAOKATSU				
	Office Action Summary	Examiner	Art Unit				
		Roy K Potter	2822				
Period for	 The MAILING DATE of this communication ap r Reply 	pears on the cover sheet with	the correspondence address				
THE N - Extens after S - If the p - If NO p - Failure Any re	DRTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. sions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a rep period for reply is specified above, the maximum statutory period to reply within the set or extended period for reply will, by statut sply received by the Office later than three months after the mailing dipatent term adjustment. See 37 CFR 1.704(b).		y be timely filed 30) days will be considered timely. S from the mailing date of this communication. IDONED (35 U.S.C. § 133).				
Status							
1)⊠ ∣	Responsive to communication(s) filed on 24 J	<i>July</i> 2003.					
2a)□ ⁻	This action is FINAL . 2b)⊠ This action is non-final.						
3)□ :	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
(closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 1	11, 453 O.G. 213.				
Dispositio	on of Claims						
4) 🗌 (Claim(s) <u>17-30</u> is/are pending in the application.						
4	4a) Of the above claim(s) is/are withdrawn from consideration.						
5) 🗌 (Claim(s) is/are allowed.						
_	Claim(s) <u>17-30</u> is/are rejected.						
•	Claim(s) is/are objected to.						
8) 📙 (Claim(s) are subject to restriction and/o	or election requirement.	·				
Application	on Papers						
9)□ T	he specification is objected to by the Examin	er.					
10)□ T	The drawing(s) filed on is/are: a)☐ acc	cepted or b) objected to by	the Examiner.				
,	Applicant may not request that any objection to the	e drawing(s) be held in abeyance	. See 37 CFR 1.85(a).				
	Replacement drawing sheet(s) including the correct	, , , , , , , , , , , , , , , , , , , ,	• • • • • • • • • • • • • • • • • • • •				
11)∟_ T	The oath or declaration is objected to by the E	xaminer. Note the attached C	Office Action or form PTO-152.				
Priority u	nder 35 U.S.C. § 119						
a)[Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority document Certified copies of the priority document Copies of the certified copies of the priority document All Copies of the certified copies of the priority document Cepter of the certified copies of the priority document Copies of the certified copies of the priority document Cepter of the certified copies of the priority document Cepter of the certified copies of the priority document Cepter of the certified copies of the priority document Cepter of the certified copies of the priority document Cepter of the certified copies of the priority document Cepter of the priority document Ce	nts have been received. Its have been received in Appointy documents have been re The part of the pa	olication No ceived in this National Stage				
Attachment(s)						
	of References Cited (PTO-892)	4) Interview Sum	nmary (PTO-413)				
3) 🔲 Inform	of Draftsperson's Patent Drawing Review (PTO-948) ation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) No(s)/Mail Date		Mail Date rmal Patent Application (PTO-152)				

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DETAILED ACTION

Claims 1 – 16 have been canceled. Claims 17-30 are pending. These claims are directed to a method of manufacturing a semiconductor device.

Claim Rejections - 35 USC § 102

Double Patenting

A rejection based on double patenting of the "same invention" type finds its support in the language of 35 U.S.C. 101 which states that "whoever invents or discovers any new and useful process ... may obtain <u>a</u> patent therefor ..." (Emphasis added). Thus, the term "same invention," in this context, means an invention drawn to identical subject matter. See *Miller v. Eagle Mfg. Co.*, 151 U.S. 186 (1894); *In re Ockert*, 245 F.2d 467, 114 USPQ 330 (CCPA 1957); and *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970).

A statutory type (35 U.S.C. 101) double patenting rejection can be overcome by canceling or amending the conflicting claims so they are no longer coextensive in scope. The filing of a terminal disclaimer <u>cannot</u> overcome a double patenting rejection based upon 35 U.S.C. 101.

Claims 17 – 30 are rejected under 35 U.S.C. 101 as claiming the same invention as that of claims 1 - 16 of prior U.S. Patent No. 6624010. This is a double patenting rejection.

Ikegami, U.S. Patent 6,624,010 discloses a method of manufacturing semiconductor devices. The method comprises the steps of forming an SOI layer 30 on silicon oxide layer 20. Cobalt 40 is formed on the SOI layer 30. CoSi is formed by annealing the structure, as explained in column 3, line 27. A silicon oxide layer 60 is formed on the CoSi layer. A contact hole 90 is formed to expose a part of the CoSi

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layer. A second anneal is then performed. The second anneal is rapid at 800 degrees Celsius, while the first is at 450 –550 degrees.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Horiuchi et al., U.S. Patent 6,800,513, discloses a method of manufacturing a semiconductor device.

Dennard et al., U.S. Patent 6,664,598 discloses a method of manufacturing a polysilicon back gated SOI MOSFET. As shown in Figure 1, oxide layer 12 isolates Si substrate 10 from SI layer 14, which is the SOI layer.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Roy K Potter whose telephone number is 571 272 1842. The examiner can normally be reached on M-F.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Roy K Potter Primary Examiner Art Unit 2822